Features

- Full-field Image Sensor 3500 x 2300 Pixels
- Pixel 10 µm x 10 µm Photo-MOS
- Image Zone: 35 mm x 23 mm
- Additional Full-frame Operating Mode: 2627 x 2300 pixels of 10 µm x 10 µm (3 zones)
- Frame Readout Through One, Two or Four Outputs
- Built-in Region of Interest (ROI) Selection
- Data Rates Up to 4 x 25 MHz (Compatibility with 10 Frames/Seconds)
- High Dynamic Range (Up to 3000), at Room Temperature and at 25 MHz Frequency
- Very Low Dark Current (MPP Mode)
- Bayer Standard Color Mosaic
- Flexibility and Performance Make Device Suitable for Digital Photography, Graphic Arts, Medical and Industrial Applications

Description

Atmel's AT71200M is a progressive scan sensor based on charge-coupled device (CCD) technology. It can be used in a wide range of applications thanks to operating mode flexibility, very high definition and high dynamic range.

The nominal photosensitive area is made up of 2300 x 3500 useful pixels and is split into four independent zones that are driven separately by four independant four-phase clocksets. Thus the sensor can be used in up to 12 main modes.

The large format and high definition make the device suitable for any application requiring precision and accuracy.

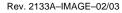
The Bayer standard RGB color mosaic has been specially designed for colorimetric applications and the three colors balanced for a 3800K standard illuminant.

Two serial registers and four independent output amplifiers offer a high-frequency functionality of up to 10 frames per second and a 12-bit dynamic range.



8M-pixel Color Image Sensor

AT71200M

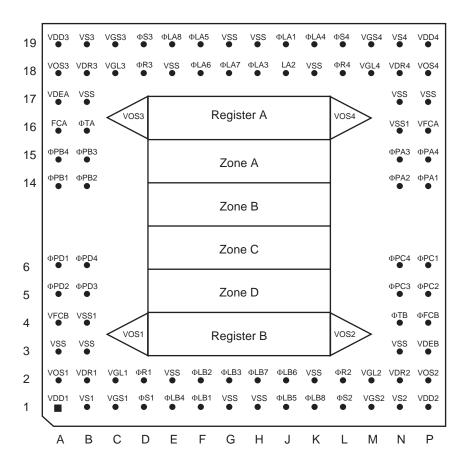






Pinout

Figure 1. AT71200M Pinout – Top View



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Table 1. AT71200M Pinout

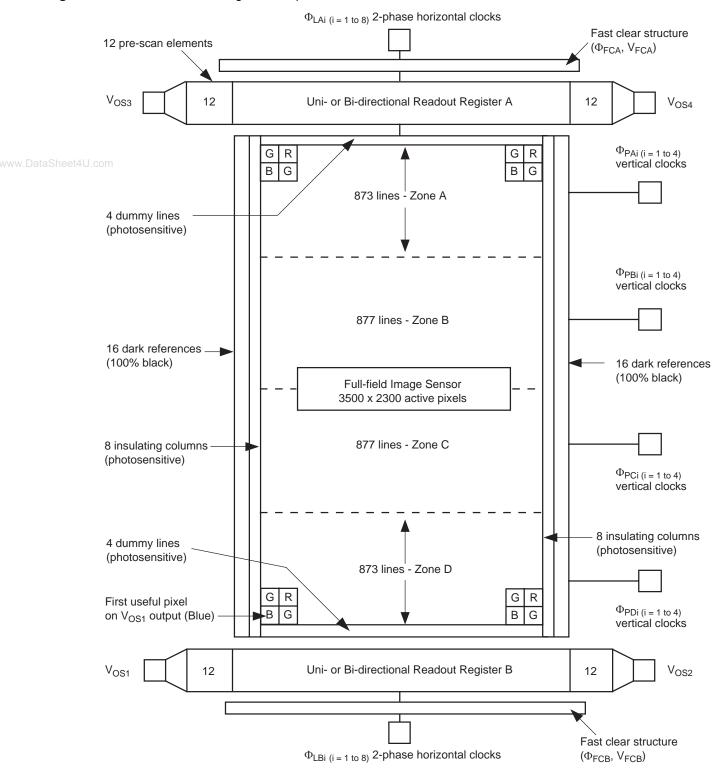
Signal Name	Pin Number	Function
ΦLB[1:8]	F1, F2, G2, E1, J1, J2, H2, K1	B readout register clocks
ΦLA[1:8]	J19, J18, H18, K19, F19, F18, G18, E19	A readout register clocks
ΦS[1:4]	D1, L1, D19, L19	Summing clocks of the outputs 1, 2, 3 and 4
VGL[1:4]	C2, M2, C18, M18	Readout gate bias of the outputs 1, 2, 3 and 4
VGS[1:4]	C1, M1, C19, M19	Output gate bias of the outputs 1, 2, 3 and 4
aSVOS[1:4]m	A2, P2, A18, P18	Output video signals 1, 2, 3 and 4
VDD[1:4]	A1, P1, A19, P19	Output amplifier drain supplies of the outputs 1, 2, 3 and 4
VS[1:4]	B1, N1, B19, N19	Output amplifier source biases of the outputs 1, 2, 3 and 4
ΦR[1:4]	D2, L2, D18, L18	Reset clocks of the outputs 1, 2, 3 and 4
VDR[1:4]	B2, N2, B18, N18	Reset bias of the outputs 1, 2, 3 and 4
ФРА[1:4]	P14, N14, N15, P15	A image zone clocks
ФРВ[1:4]	A14, B14, B15, A15	B image zone clocks
ФРС[1:4]	P6, P5, N5, N6	C image zone clocks
ΦPD[1:4]	A6, A5, B5, B6	D image zone clocks
ΦΤΑ, ΦΤΒ	B16, N4	Transfer gates from the image zone to the readout registers A and B respectively
VDEA, VDEB	A17, P3	Shield drains
VFCA, VFCB	P16, A4	Region of interest drains
ФГСА, ФГСВ	A16, P4	Region of interest clocks
VSS	A3, B3, B4, E2, G1, H1, K2, M3, B17, E18, G19, H19, K18, N16, N17, P17	Substrate bias





Block Diagram

Figure 2. AT71200M Block Diagram - Top View



Architectural Overview

General Parameters

Table 2. General Parameters

Parameters	Value
Pixel size	10 μm x 10 μm
Number of useful pixels on one line	2300
Number of useful lines	3500
Number of readout register	2
Number of outputs	4 ⁽¹⁾
MPP technology	yes
Region of interest structures on readout registers	yes
Built-in antiblooming	no
Pixel mode	4 phase
Readout register mode	2 phase

1. The design allows the full frame to be read through one, two or four outputs. Note:

Top to Bottom

Vertical Characteristics - AT71200M is made up of four zones, A, B, C and D. The configuration of each zone is shown in Table 3.

Table 3. Vertical Characteristics

Zone	Configuration	
Λ.	4 dummy photosensitive lines	
A	873 active lines, 100% photosensitive	
В	877 active lines, 100% photosensitive	
С	877 active lines, 100% photosensitive	
D	873 active lines, 100% photosensitive	
D	4 dummy photosensitive lines	

Horizontal **Characteristics**

Table 4 gives information on the characteristics seen by one output (V_{OS1}, V_{OS2}, V_{OS3} or V_{OS4}) in different readout modes.

Table 4. Horizontal Characteristics

	Readout Mode				
Characteristic	One Output	Two Outputs on Same Register			
Pre-scan elements	12	12			
Dark references	16	16			
Insulating elements	8	8			
Useful pixels	2300	1150			





Color Mosaic Architecture

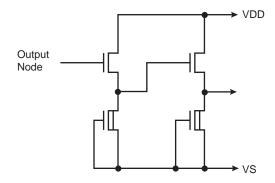
The color mosaic architecture corresponds to the Bayer standard represented by the following grid:

G	R	G	R
В	G	В	G
G	R	G	R
В	G	В	G

Output Amplifiers

The charge packets are clocked to the output nodes and the charges are converted to voltages. The potential at the output node is read through two stage source follower amplifiers. Refer to Figure 3.

Figure 3. On-chip Output Amplifier Structure



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Absolute Maximum Ratings*

Storage Temperature Range.	55°C to +150°C
Operating Temperature Range	-40°C to +85°C
Thermal Cycling	15°C/mn

*NOTICE:

Stresses above those listed under Absolute Maximum Ratings may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

Electrical limits of applied signals are given in Table 5.

Shorting the video output to V_{SS} or V_{DD} , even temporarily, can permanently damage the output amplifier.

Due to MPP mode or negative voltages, image zone gates and region of interest gates do not include ESD protection. To avoid degradation, the devices (including pins and package) should be handled with a grounded bracelet and stored on conductive layer used for shipment.

Table 5. Maximum Applied Voltages⁽¹⁾

Signal Name	Parameter	Min	Max	Unit
ΦLA[1:8]	Readout A Register Clocks	-0.3	+15	V
ΦLB[1:8]	Readout B Register Clocks	-0.3	+15	V
ФЅ[1:4]	Summing Gate	-0.3	+15	V
VGL[1:4]	Readout Gate	-0.3	+15	V
VGS[1:4]	Output Gate	-0.3	+15	V
VOS[1:4]	Output Video Signal	-0.3	+15	V
VDD[1:4]	Amplifier Drain Supply	-0.3	+15	V
VS[1:4]	Source Bias	-0.3	+15	V
ΦR[1:4]	Reset Gate	-0.3	+15	V
VDR[1:4]	Reset Bias	-0.3	+15	V
ФРА[1:4]	Image Zone A Clocks	-15 and ΦPA[other] - 20	+15 and ΦPA[other] + 20	V
ФРВ[1:4]	Image Zone B Clocks	-15 and ΦPB[other] - 20	+15 andΦPB[other] + 20	V
ФРС[1:4]	Image Zone C Clocks	-15 and ΦPC[other] - 20	+15 and ΦPC[1:4] + 20	V
ΦPD[1:4]	Image Zone D Clocks	-15 and ΦPD[other] - 20	+15 and ΦPD[other] + 20	V
ΦΤΑ	Transfer Gates Zone A	ΦLA - 15 and ΦPA[4] - 15	+15 and ΦPA[4] + 15	V
ФТВ	Transfer Gates Zone B	ΦLB - 15 and ΦPD[4] - 15	+15 and ΦPD[4] + 15	V
VDEA, VDEB	Shield Drains	-0.3	+15	V
VFCA, VFCB	Region Of Interest Drains	-0.3	+15	V
ФЕСА	Region Of Interest Gates Zone A	ΦLA[1:8] - 15	+15	V
ФЕСВ	Region Of Interest Gates Zone B	ΦLB[1:8] - 15	+15	V
VSS	Substrate Bias		0	V

Note: 1. If not specified, all voltages are applied with respect to the substrate VSS.





DC Characteristics

Symbol	Parameter	Minimum	Typical	Maximum	Unit	Typical Currents
V _S ⁽¹⁾	Source bias	0	0	1	V	< 12 mA
V _{DD} ⁽¹⁾	Amplifier drain supply	14.5	15	15.5	V	< 12 mA
V_{SS}	Substrate bias	0	0		V	_
V _{GS}	Output gate	7	7.5	8	V	< 1 µA
V_{DR}	Reset diode	13.5	14	14.5	V	< 5 µA
V_{GL}	Readout gate	3	3.5	4	V	< 1 µA
Sheet4DEom	Shield drain	3	5	6	V	< 1 µA
V_{FC}	Regions of interest drains	12.5	13	13.5	V	< 5 µA

Note: 1. If corresponds to inactive output, may be stated to [3V, 7V] in order to reduce power consumption.

Drive Clock Characteristics

Symbol	Parameter	State	Minimum	Typical	Maximum	Unit	Remarks
		Low	-10	-9	-8	V	For each A, B, C and D
$\Phi_{Pij}^{(1)(2)}$	Image Zone Clocks	High	+2.5	+3	+3.5	V	zone, the typical capacitances to drive are C_{Pij} approx. 12 nF
		Low	0	0	+0.5	V	After the eight clocks have been grouped together to form the two clocks Φ_{L1}
Φ _{Lmn} ⁽³⁾⁽⁴⁾ taSheet4U.com	Readout Register Clocks	High	+7.5	+8	+9	V	and Φ_{L2} , the typical capacitances to drive for each register A or B are $C_{\Phi L1}$ approx. 310 pF and $C_{\Phi L2}$ approx. 310 pF
- (2)		Low	0	0	+0.5	V	For each Φ_{Sj} , the typical
$\Phi_{Sj}^{\;(2)}$	Summing Gates	High	+7.5	+8	+9	V	capacitance to drive is $C_{\Phi Sj}$ approx. 40 pF
(0)		Low	+1	+2	+3	V	For each Φ_{Rj} , the typical
$\Phi_{Rj}^{\;(2)}$	Reset Gates	High	+8	+9	+10	V	capacitance to drive is $C_{\Phi Rj}$ approx. 40 pF
(0)		Low	-6	-5	-4	V	For each Φ_{Tm} , the typical
$\Phi_{Tm}^{(3)}$	Transfer Gates	High	+2.5	+3	+3.5	V	capacitance to drive is $C_{\Phi Tm}$ approx. 150 pF
(0)		FC inactive	-3.5	-2.5	-2	capacitance t	For each Φ_{FCm} , the typical capacitance to drive is
$\Phi_{FCm}^{(3)}$	Region of Interest Gates	terest Gates Low 0 0	+0.5	V	С _{ФFCm} approx. 50 pF		
		High	+3.5	+4	+4.5	V	

Notes: 1. i = A, B, C or D

2. j = 1, 2, 3 or 4

3. m = A or B

4. n = 1, 2, 3, 4, 5, 6, 7 or 8





Operating Modes

For the required readout mode, the vertical and horizontal clocks must be tied together externally as shown in Figure 4.

Figure 4. Operating Modes

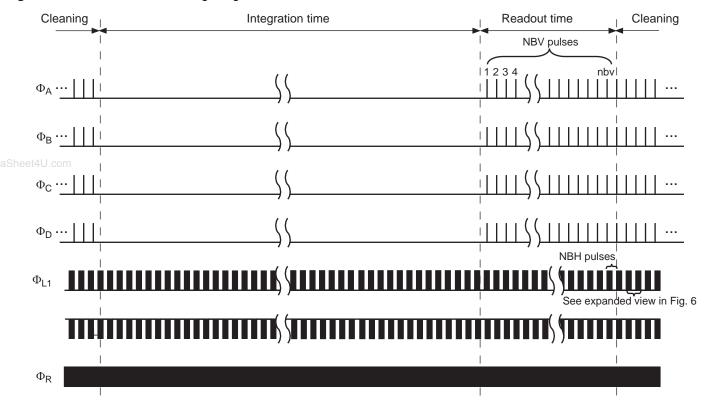
3508 transfers min NBV = 3508	3508 transfers min NBV = 3508	1754 transfers min NBV = 1754	2631 transfers min NBV = 2631
1-2-3 modes	4-5-6 modes	7-8-9 modes	10-11-12 modes
ΦΡΑΙ=ΦΡΒΙ=ΦΡΟΙ=ΦΡΟΙ= ΦΑ ΦΡΑ2=ΦΡΒ2=ΦΡΟ2=ΦΡΟ2= ΦΒ ΦΡΑ3=ΦΡΕ3=ΦΡΟ3=ΦΡΟ3= ΦΟ ΦΡΑ4=ΦΡΕ4=ΦΡΟ4=ΦΡΟ4= ΦΟ	ΦΡΑ1=ΦΡΒ1=ΦΡC1=ΦΡD1= ΦΑ ΦΡΑ2=ΦΡΒ2=ΦΡC2=ΦΡD2= ΦΒ ΦΡΑ3=ΦΡΒ3=ΦΡC3=ΦΡD3= ΦC ΦΡΑ4=ΦΡΒ4=ΦΡC4=ΦΡD4= ΦΒ	ΦΡΑ1=ΦΡΒ1=ΦΡC1=ΦΡD1= ΦΑ ΦΡΑ2=ΦΡΒ2=ΦΡC2=ΦΡD2= ΦΒ ΦΡΑ3=ΦΡΒ3=ΦΡC3=ΦΡD3= ΦC ΦΡΑ4=ΦΡΒ4=ΦΡC4=ΦΡD4= ΦD	ФРА1=ФРВ1=ФРС1=ФРD1= ФА ФРА2=ФРВ2=ФРС2=ФРD2= ФВ ФРА3=ФРВ3=ФРС3=ФРD3= ФС ФРА4=ФРВ4=ФРС4=ФРD4= ФD
ΦTA = Low Level ΦTB = ΦA	ΦTA = ΦA ΦTB = Low Level	ΦΤΑ = ΦΑ ΦΤΒ = ΦΑ	ΦΤΑ = ΦΑ ΦΤΒ = ΦΑ

3 Inactive 4 3 4 3 4 3 4 2336 PIXELS PERIODS NBH = 2336Mode1 Mode4 Mode7 4-7-10 modes Mode10 Φ LA1= Φ LA3= Φ LA5= Φ LA8= Φ L1 Φ LA2= Φ LA4= Φ LA6= Φ LA7= Φ L2 1-7-10 modes HORIZONTAL TRANSFER ΦLB1=ΦLB4=ΦLB5=ΦLB7=ΦL1 ΦLB2=ΦLB3=ΦLB6=ΦLB8=ΦL2 2 2 Inactive 1 2 2 Inactive 3 4 3 4 3 4 3 4 2336 PIXELS PERIODS NBH = 23365-8-11 modes Mode2 Mode5 Mode8 Mode11 ΦLA1=ΦLA4=ΦLA5=ΦLA7=ΦL1 ΦLA2=ΦLA3=ΦLA6=ΦLA8=ΦL2 2-8-11 modes Φ LB1= Φ LB3= Φ LB5= Φ LB8= Φ L1 Φ LB2= Φ LB4= Φ LB6= Φ LB7= Φ L2 2 2 Inactive 2 1 2 3 Inactive 4 3 3 3 $\leftrightarrow \rightarrow$ 4 \leftrightarrow 4 \leftrightarrow 4 1186 PIXELS PERIODS NBH = 1186Mode3 Mode9 Mode12 6-9-12 modes Mode6 ФТ.А2=ФТ.А3=ФТ.А6=ФТ.А7=ФТ.2 3-9-12 modes ΦLB1=ΦLB4=ΦLB5=ΦLB8=ΦL1 ΦLB2=ΦLB3=ΦLB6=ΦLB7=ΦL2 2 2 2 2 Inactive

Note: Symbols ΦA , ΦB , ΦC and ΦD correspond to the clocks described in the full-frame mode timing diagrams. Abbreviations NBV and NBH correspond respectively to the vertical and horizontal number of transfers. The unused horizontal clocks (ΦL , ΦR , ΦS) must be stated to higher level of ΦL .

Timing Diagrams

Figure 5. Full-frame Mode Timing Diagram



Note: ΦA , ΦB , ΦC , ΦD , $\Phi L1$ and $\Phi L2$ (command phases) and NBV and NBH (number of vertical transfers and number of horizontal transfers respectively) are defined in Figure 4.



Figure 6. Line Timing Diagram

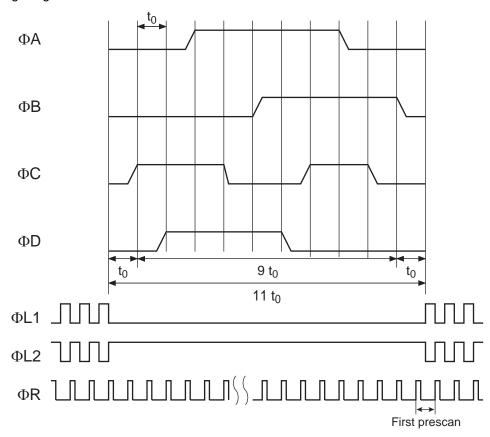
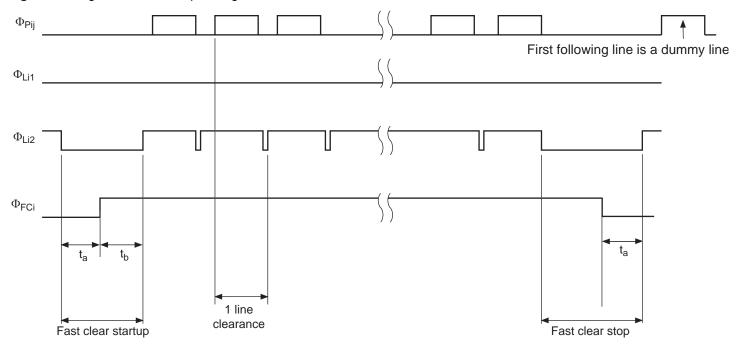


Figure 7. Region of Interest Operating Mode



Note: Typical values of t_a , t_b , t_c , $t_a \ge 150$ ns, $t_b \ge 150$ ns, $t_c \ge 150$ ns

Table 6. Typical TR and TF (Time Rise, Time Fall) for Phases

Phase	Time
Φ_{P1}	500 ns
Φ_{P2}	500 ns
Φ_{P3}	500 ns
Φ_{P4}	500 ns
$\Phi_{\sf FC}$	50 ns
V _{FC}	50 ns
Φ_{L1}	10 ns
Φ_{L2}	10 ns
Φ_{S}	10 ns
Фр	4 ns

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Frame Rate Characteristics

Table 7. Frame Rate Characteristics

One Output		Two Outputs	Four Outputs	
(Modes 1, 2, 3, 4)		(Modes 13, 14)	(Mode 15)	
Without binning	Typical 2.8 fps	Typical 5.1 fps		

Note: Table 7 gives typical values for full-frame mode where:

- Horizontal pixel frequency = 25 MHz
- Vertical transfer time $T_V = 11 \text{ x } t_0 = 10 \text{ }\mu\text{s}$ (delay times before and after line transfer $t_1 = t_2 = t_0$)
- Integration time = 0s:

Table 8. Electrical and Miscellaneous Characteristics

Symbol	Parameters	Minimum	Typical	Maximum	Unit
V_{REF}	DC output level		10		V
Z _{OUT}	Output impedance		230		Ohms
I _{DD} ⁽¹⁾	Output amplifier supply current		10	15	mA
C _{VF}	Charge-to-voltage conversion factor	7.3	7.6	8.0	μV/e-
T _V	Vertical transfer time	5	10		μs
FH	Maximum Readout pixel frequency	25	_	_	MHz

Note: 1. For each output.



Electrooptical Data

Table 9. Performance Data⁽¹⁾

Symbol	Parameters	Minimum	Typical	Maximum	Unit
V _{SAT}	Pixel saturation output voltage	500	600	700	mV
R-Blue ⁽²⁾	Responsivity blue	0.45	0.60		V/(µJ/cm²)
R-Green ⁽²	Responsivity green	0.45	0.60		V/(µJ/cm ²)
R-Red ⁽²⁾	Responsivity red	0.70	0.92		V/(µJ/cm²)
R-Blue ⁽²⁾	Responsivity blue		0.19		V/(lux.s)
R-Green ⁽²	Responsivity green		0.19		V/(lux.s)
R-Red ⁽²⁾	Responsivity red		0.25		V/(lux.s)
PRNU	Photo response non uniformity, σ		1	6	% VOS
DSI1	Image zone MPP mode		0.3		mV/s
DSI2	Image zone non-MPP mode		60		mV/s
DSR	Readout register (non-MPP mode)		150		mV/s
VDS ⁽³⁾	Average dark signal		7	20	mV
DSNU ⁽³⁾	Dark signal non-uniformity, σ		3.5	5.5	mV
V _N	Temporal RMS noise in darkness at BW = 150 MHz		270		μV
DR	Dynamic range		67		dB
	Linearity		1		%
MTF ⁽⁴⁾	Modulated transfer function		86		%
VCTE ⁽⁵⁾	Vertical charge transfer efficiency (per stage)	0.99995	0.999998		_
HCTE ⁽⁵⁾	Horizontal charge transfer efficiency (per stage)	0.99995	0.999998		_

Notes: 1. General measurement conditions:

 $T_C = 25^{\circ}C$ (chip temperature)

Vertical transfer time TV = 10 ms

Readout pixel frequency $F_H = 5 \text{ MHz}$

Readout through 4 outputs and standard mode 9 (see figure 4) 3200K Halogen lamp with 2 mm BG38 filter at f/11 aperture

2. Blue, Green, Red channels

The responsivity are well balanced for 3800K source

- 3. Integration time Ti = 10s in darkness
- 4. Green
- 5. Output voltage > 10% VSAT

Figure 8. Typical Spectral Response with BG38 Infrared Filter (2 mm thickness), light source powered between 400 and 700 nm

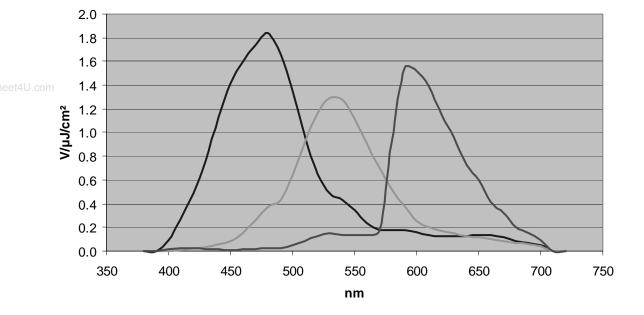




Image Grade

Table 10 gives results of image grade testing.

Table 10. Image Grade⁽¹⁾

	Blemishes		Cluster 1		Cluster 2		Column	
Grade	Total	D min ⁽²⁾	Total	D min ⁽²⁾	Total	D min ⁽²⁾	Total	D min ⁽²⁾
Е	≤ 500	3	≤ 30	50	≤ 6	100	≤ 4	150
Н	≤ 300	3	≤ 10	50	0		0	

Notes: 1. Testing has been carried out under the following conditions:

Operating temperature: 25°C (unless otherwise specified)

Illumination conditions: 3200K Halogen lamp with BG38 Infrared filter and f/11 aperture

Integration time = 10s in darkness

www.DataSheet4U.com Test under illumination at 50% of saturation level

Standard mode, $T_V = 10 \mu s$, FH = 5 MHz

2. D min: Minimum number of pixels separating defects in any direction. All occurences are non-contiguous.

Definitions

Defect Sizes

Туре	Description
Blemish	1 x 1 defect
Cluster	Blemish grouping of not more than a given number of adjacent defects: $1 \times 1 < \text{cluster } 1 \text{ size} \le 2 \times 2$ $2 \times 2 < \text{cluster } 2 \text{ size} \le 5 \times 5$
Column	One-pixel-wide column with more than seven contiguous defective pixels

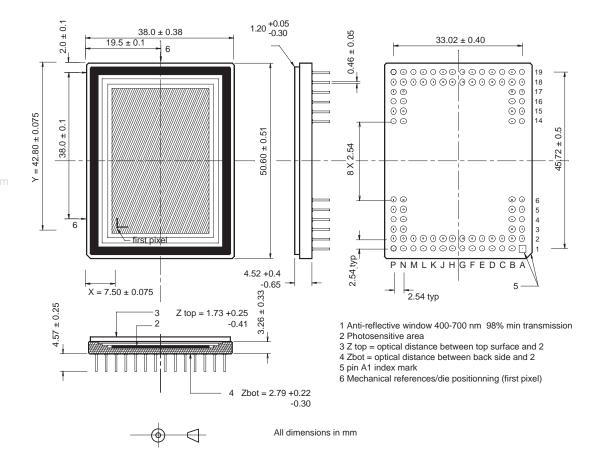
Defects in Darkness

Туре	Description
Blemish/Cluster	Pixel signal deviation of more than 200 mV from the average output signal
Column	Column signal deviation of more than 20 mV from the average output signal

Defects under Illumination

Туре	Description
Blemish/Cluster	Pixel deviation of more than +20% or -30% from the average output signal
Column	Column deviation of more than 10% from the average output signal

Package Drawing

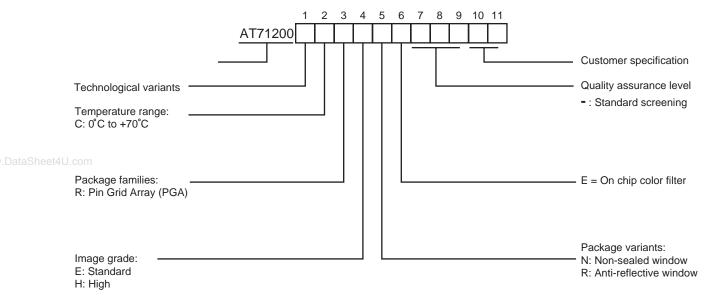


<u>AIMEL</u>



Ordering Information

Figure 9. Ordering Code Key



The following part numbers are available:

- AT71200MCRERE: version grade E
- AT71200MCRHRE: version grade H



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